

FIG. 1

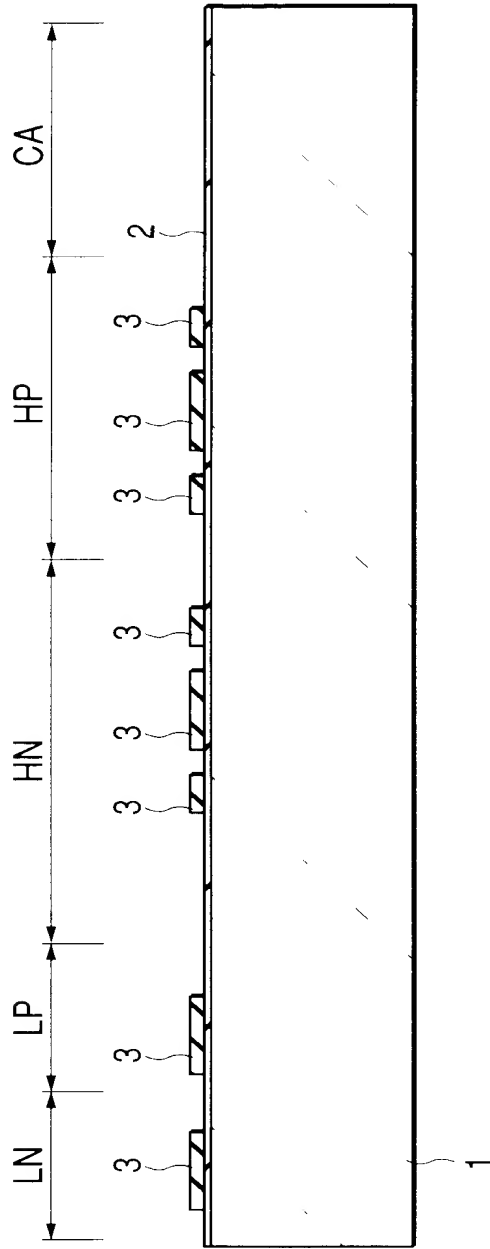
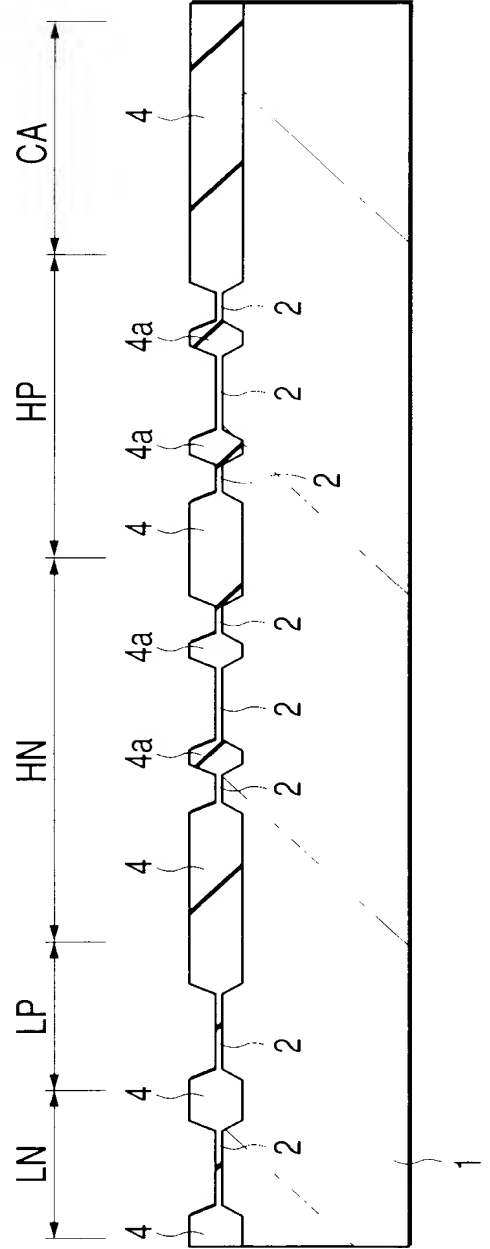


FIG. 2



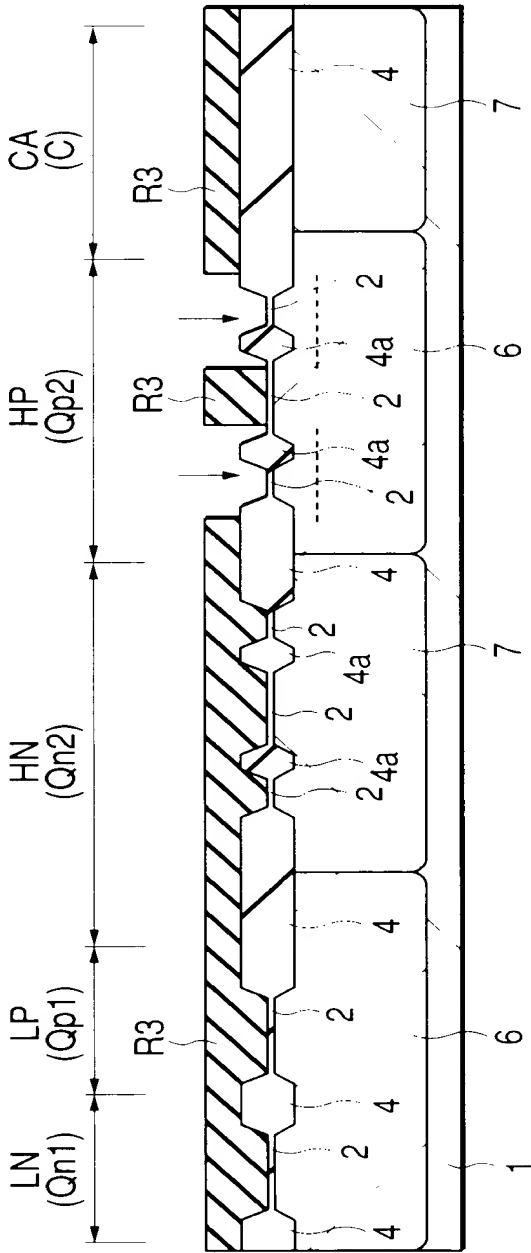


FIG. 5

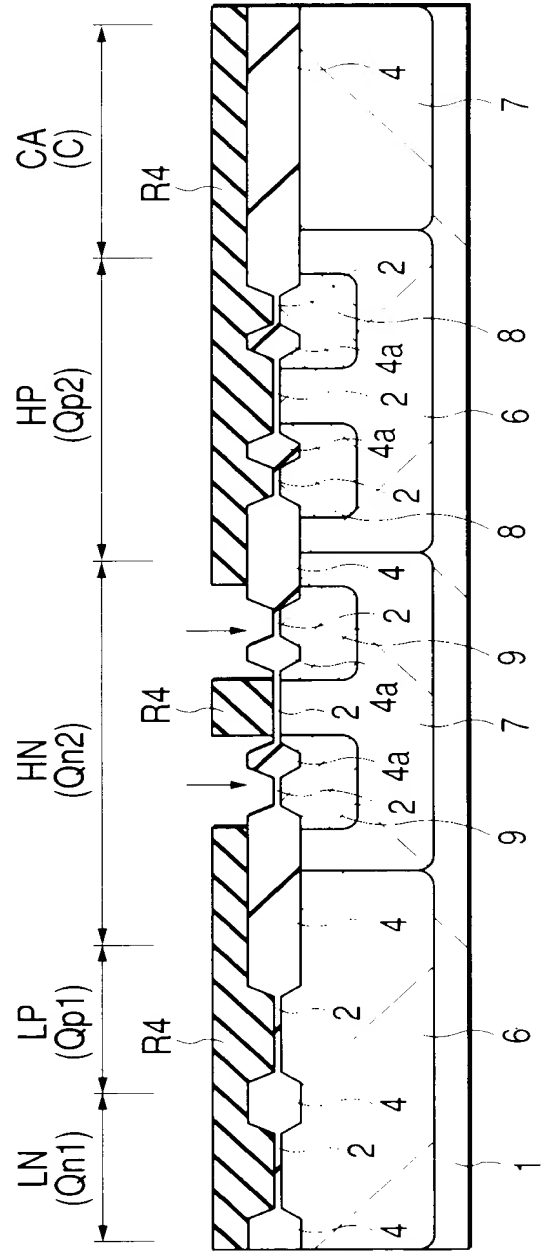


FIG. 6

FIG. 7

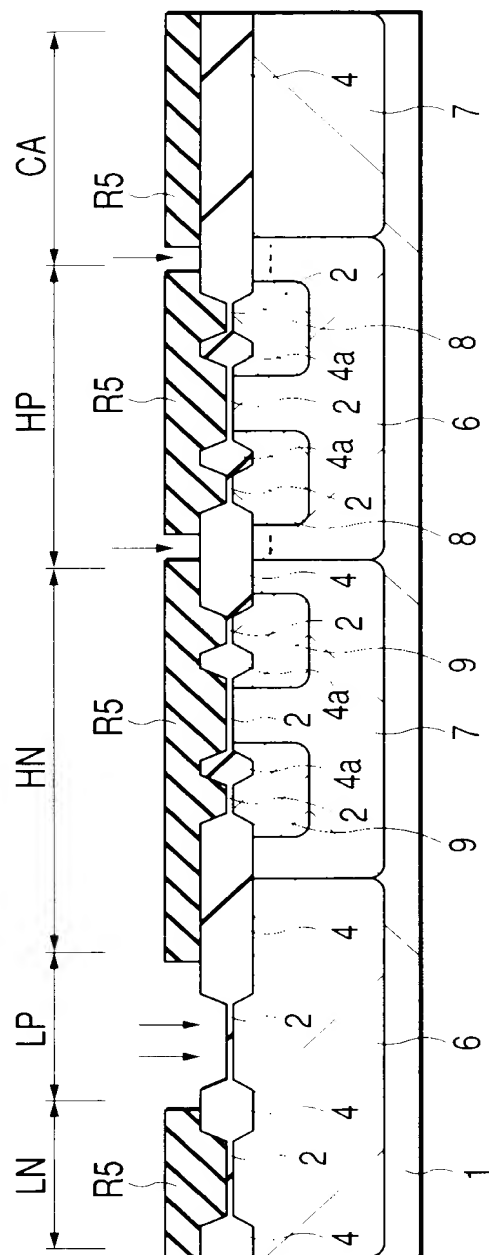


FIG. 8

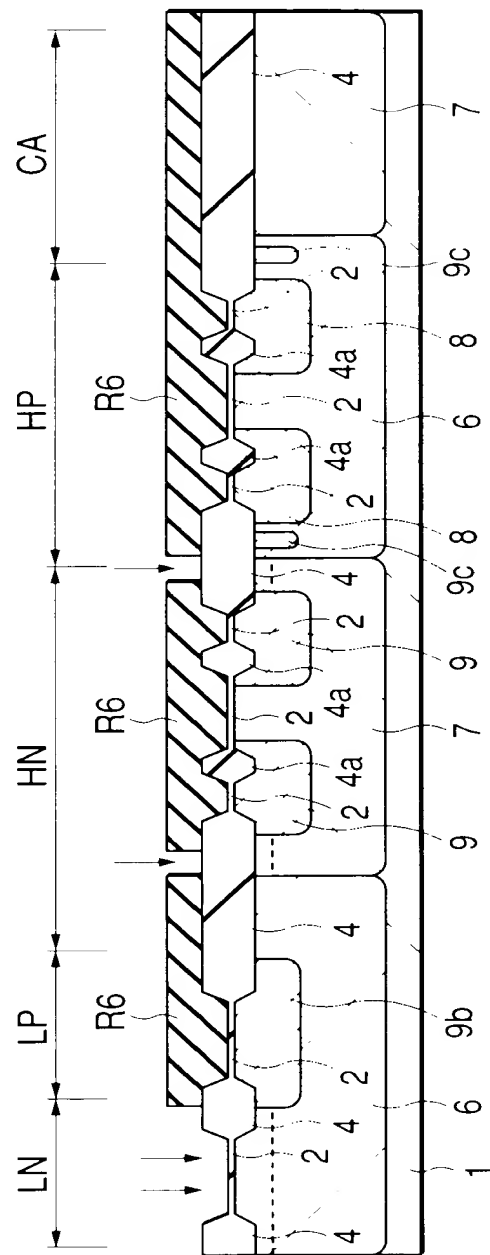


FIG. 9

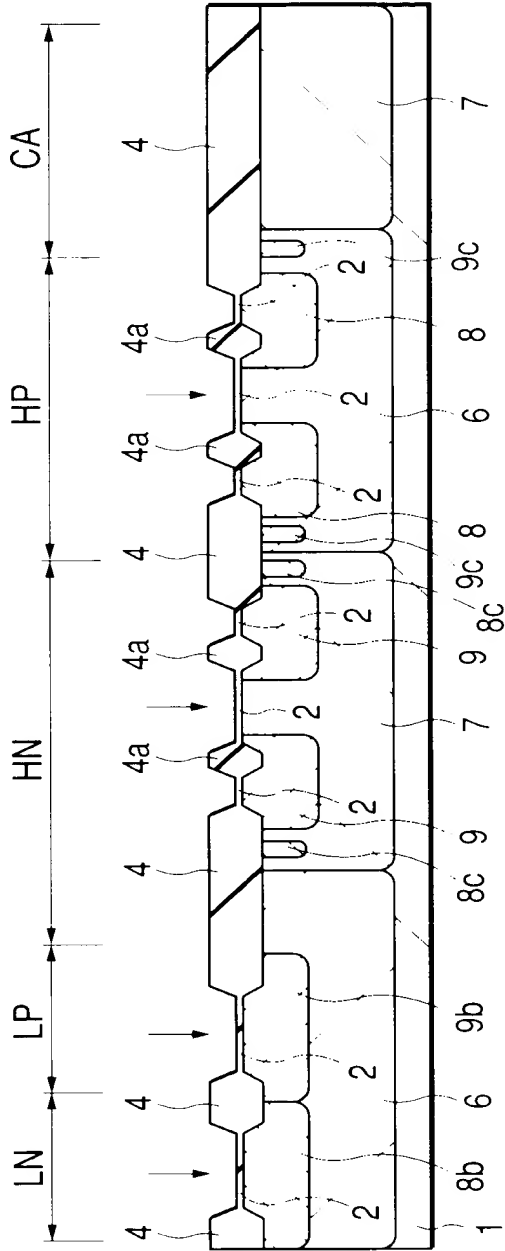


FIG. 10

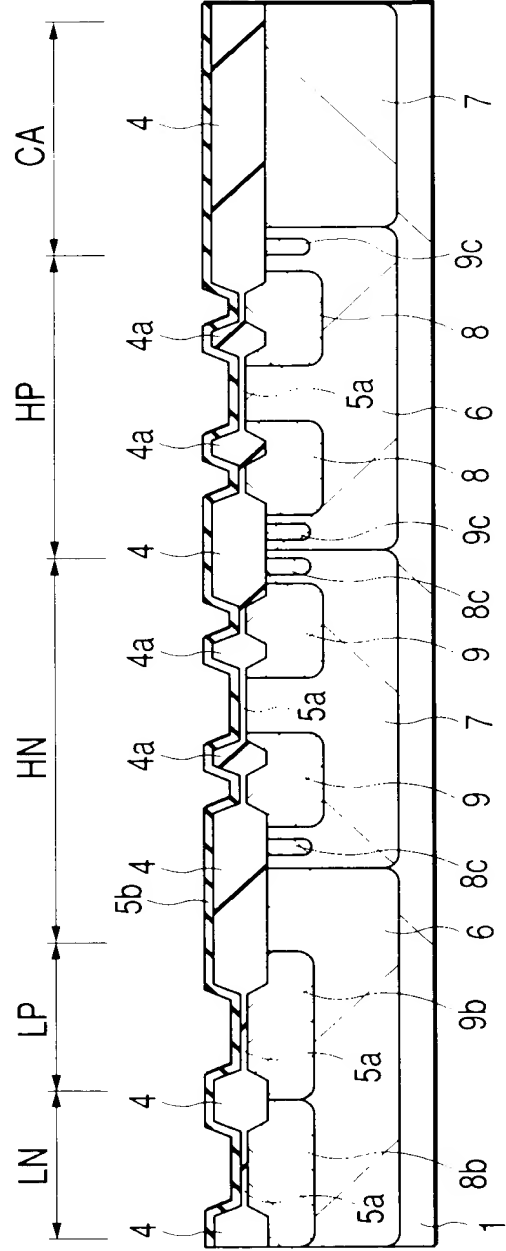


FIG. 11(a)

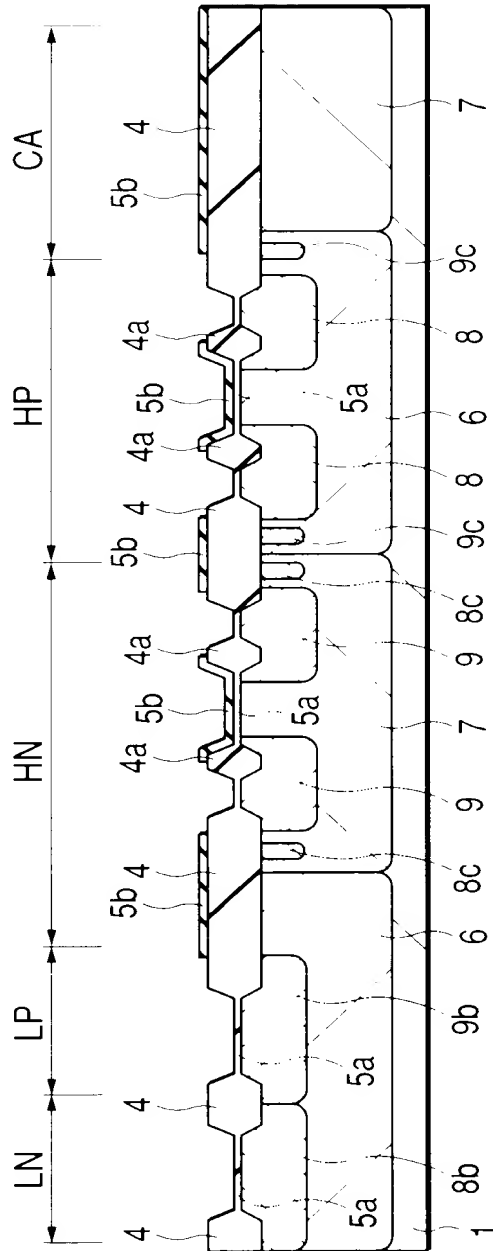


FIG. 11(b)

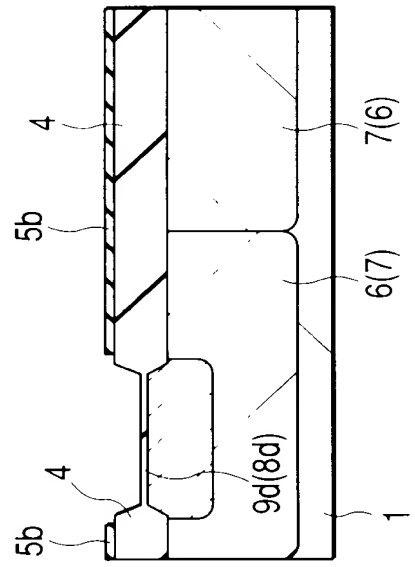


FIG. 12

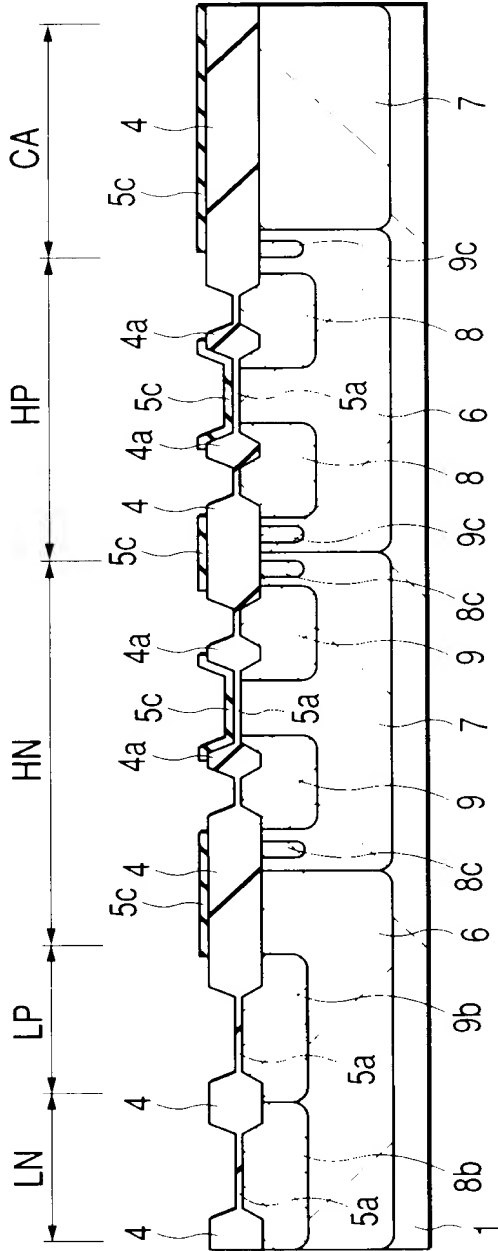


FIG. 13

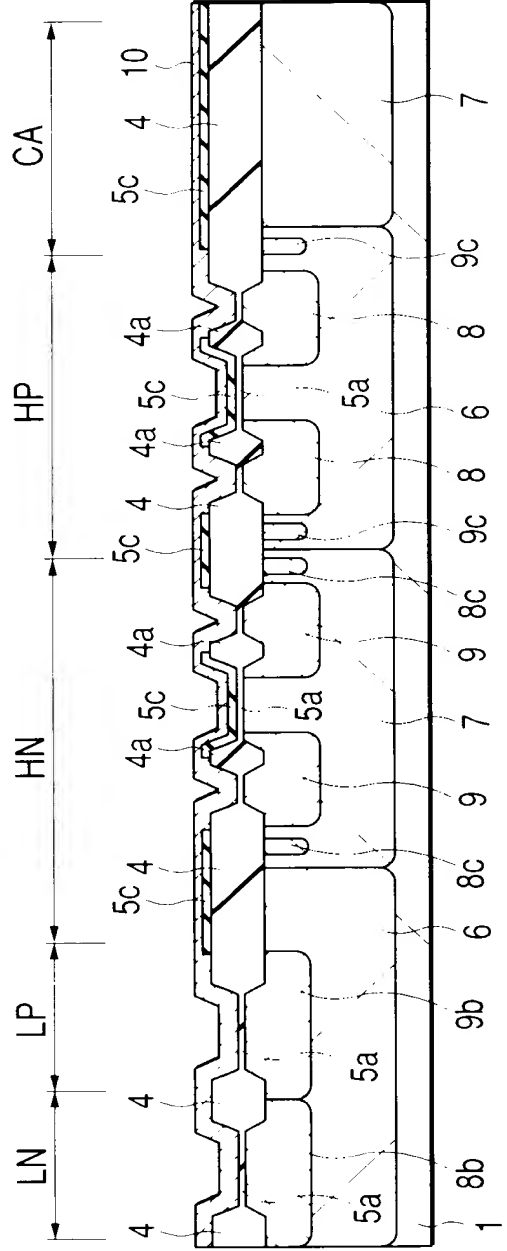


FIG. 14(a)

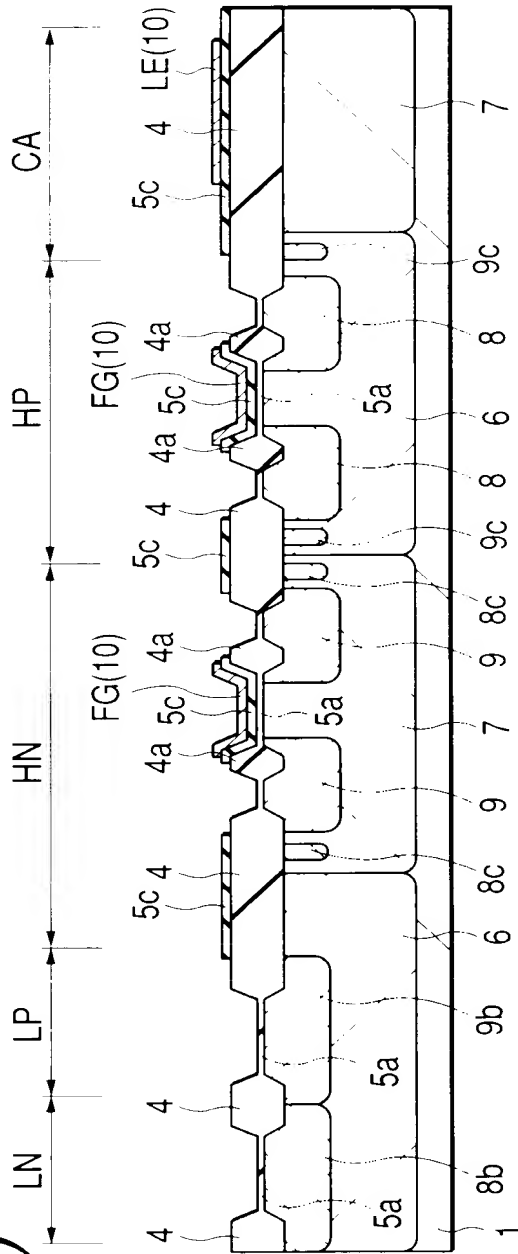


FIG. 14(b)

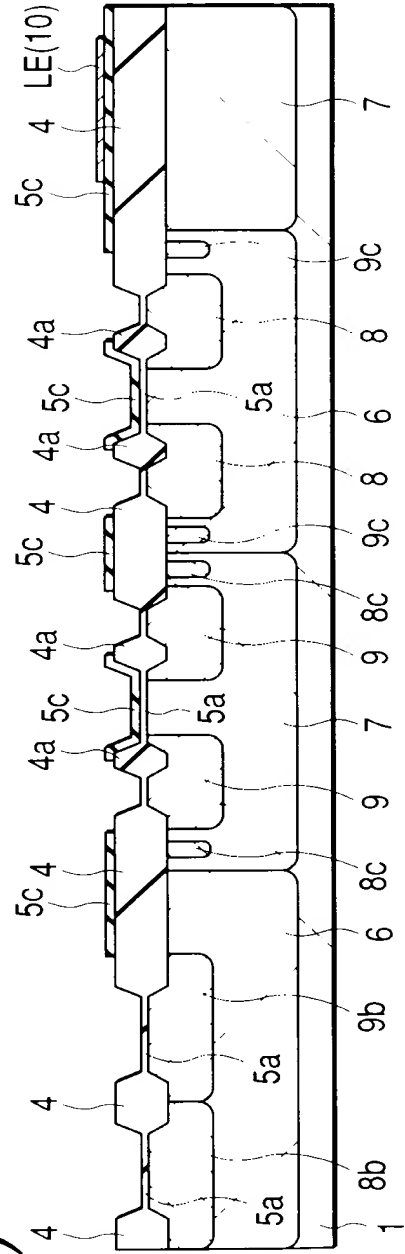
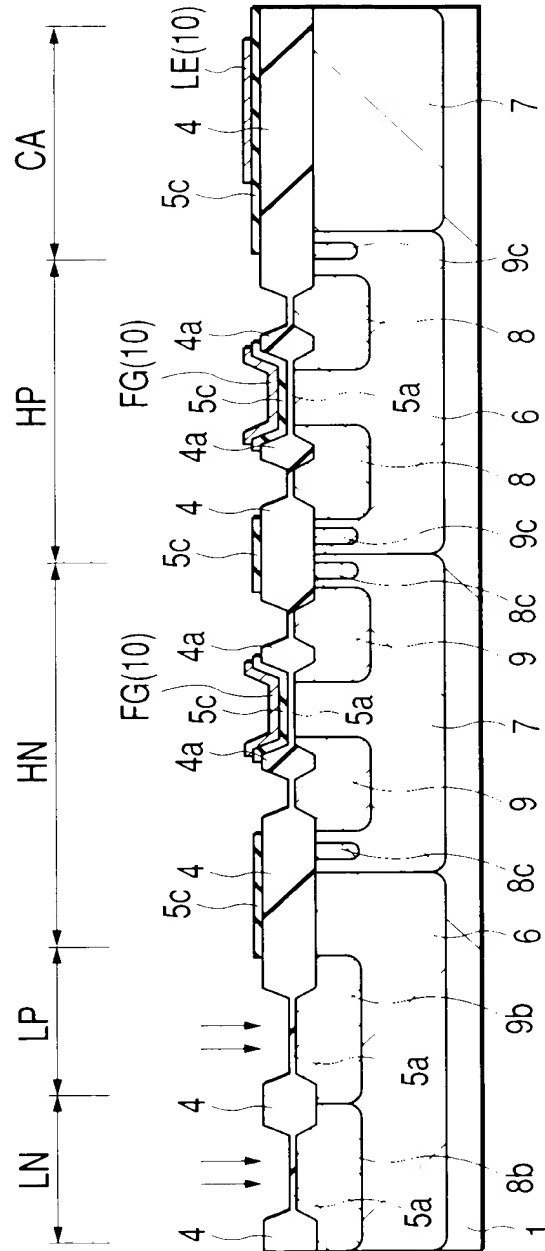


FIG. 15



This diagram shows a cross-sectional view of a semiconductor device. The device consists of several layers and regions. At the top, there is a layer labeled 'CA'. Below this, there are regions labeled 'LN', 'LP', 'HN', 'HP', and 'CA' from left to right. The main body of the device is divided into several vertical sections. The leftmost section is labeled 'SG(11)' and contains regions '16S' and '16S'. The next section is labeled 'SG(11)' and contains regions '16S' and '16S'. The third section is labeled 'FG(10)' and contains regions '5c' and '5c'. The fourth section is labeled 'FG(10)' and contains regions '5c' and '5c'. The fifth section is labeled 'UE(11)' and contains regions '5c' and '5c'. The rightmost section is labeled 'LE(10)' and contains regions '5c' and '5c'. The device is divided into several horizontal layers, with labels '4', '4a', '4b', '4c', '4d', '4e', '4f', '4g', '4h', '4i', '4j', '4k', '4l', '4m', '4n', '4o', '4p', '4q', '4r', '4s', '4t', '4u', '4v', '4w', '4x', '4y', '4z' indicating different layers or regions. The bottom of the device is labeled '8b'.



FIG. 22(a)

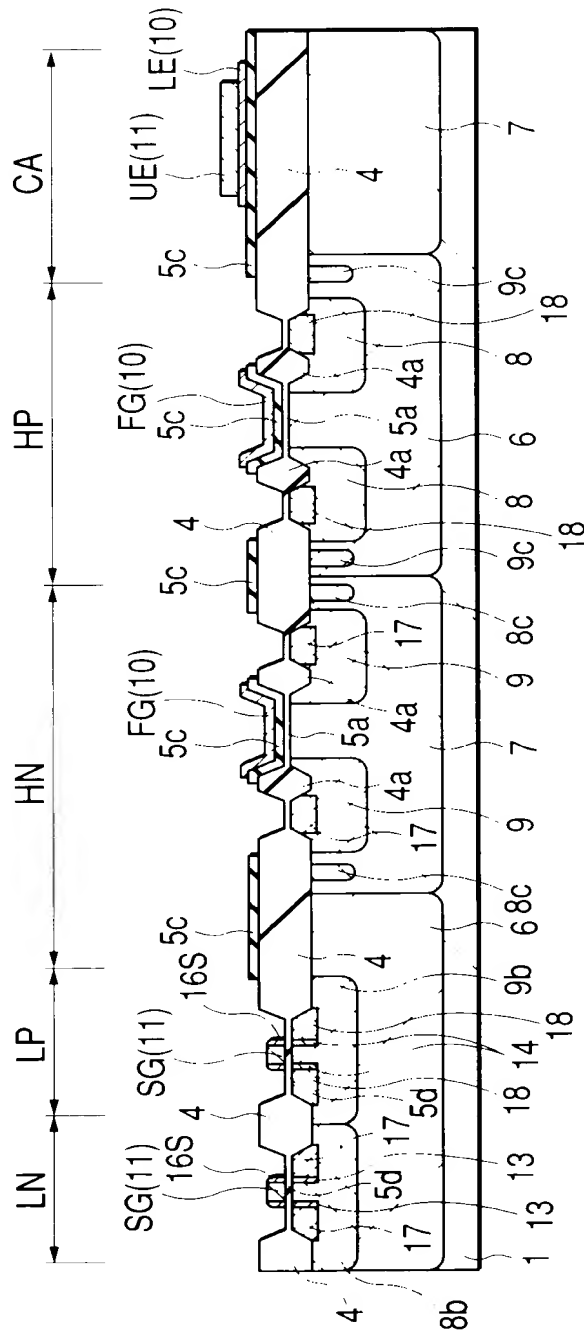


FIG. 22(b)

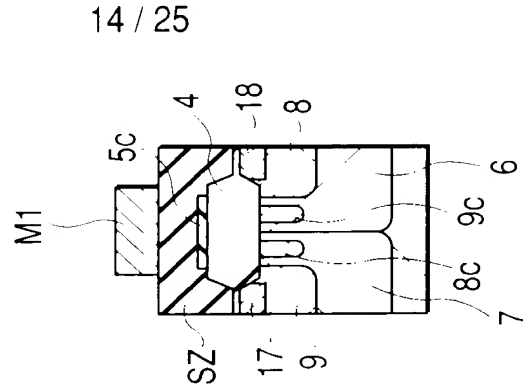


FIG. 23

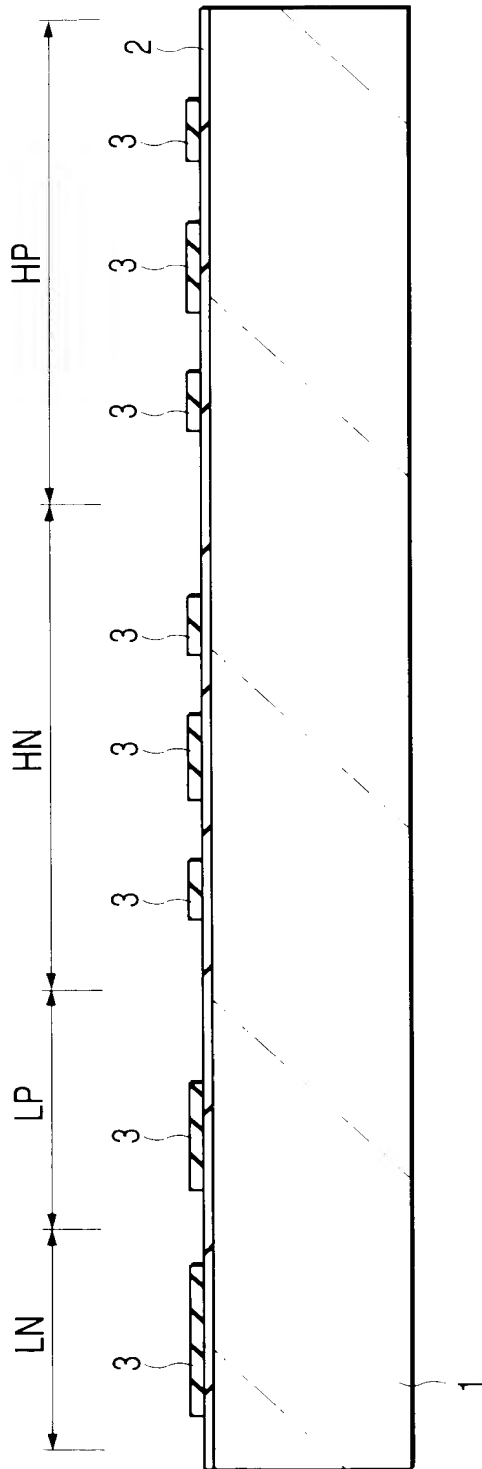


FIG. 24

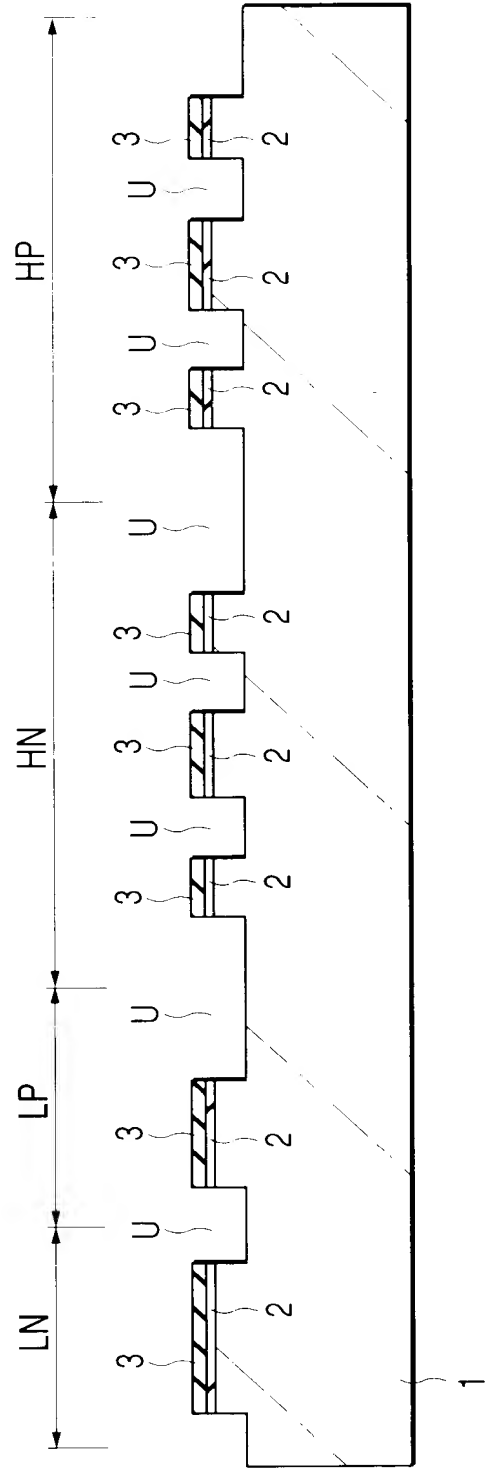


FIG. 26(a)

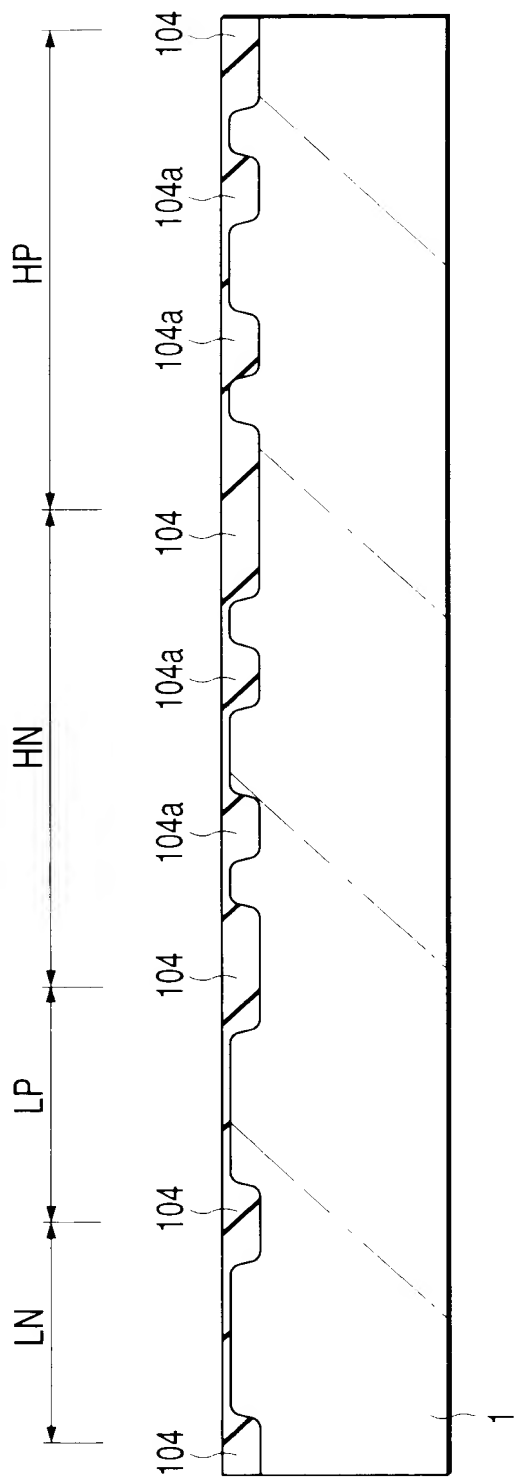


FIG. 26(b)

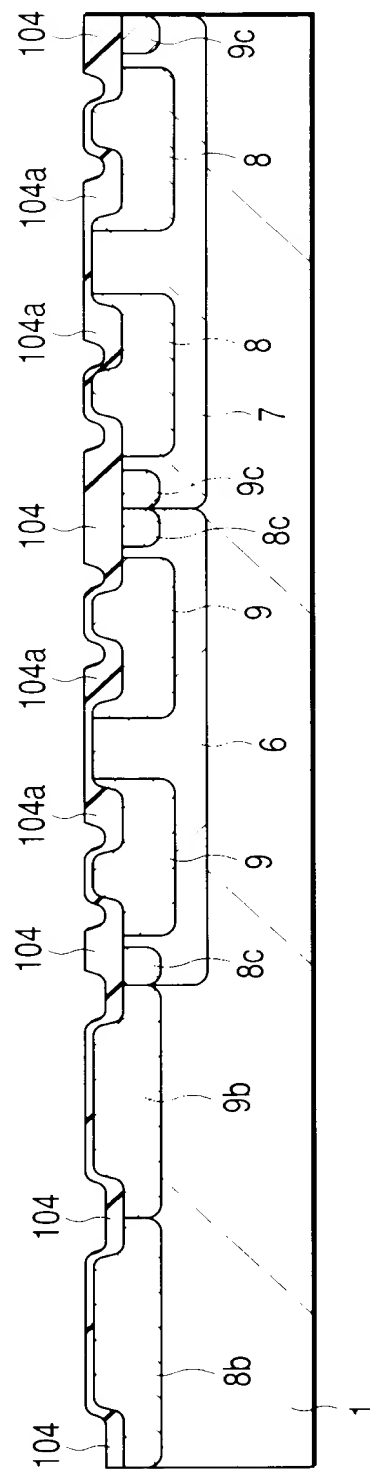


FIG. 27

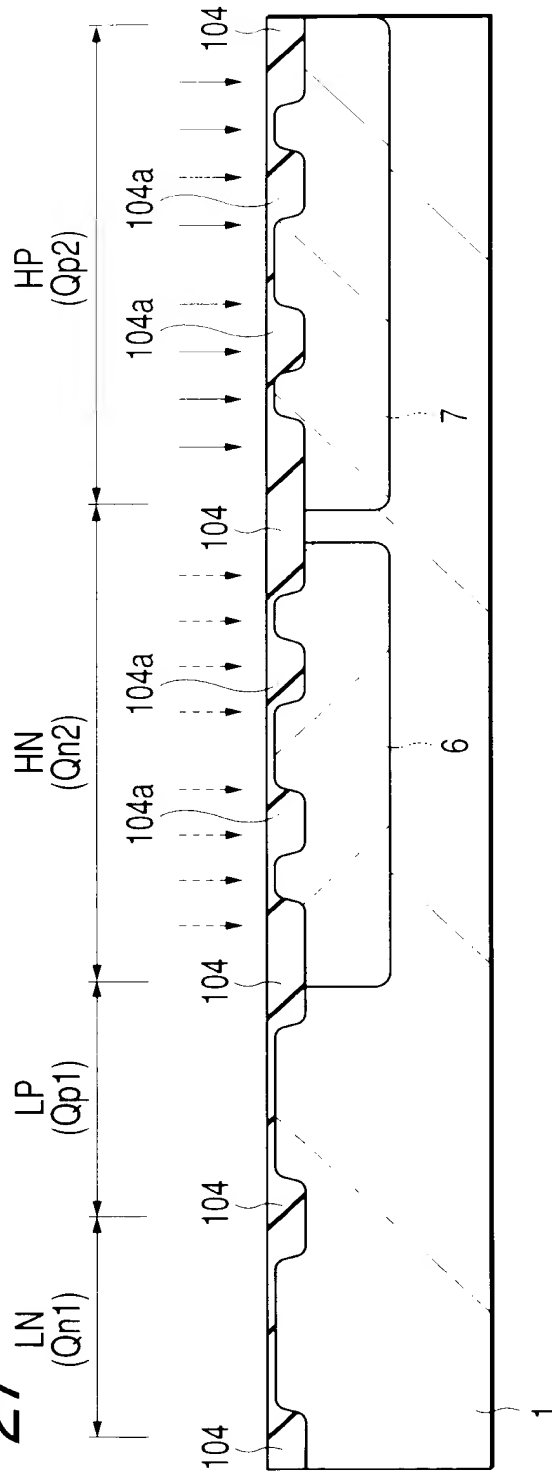
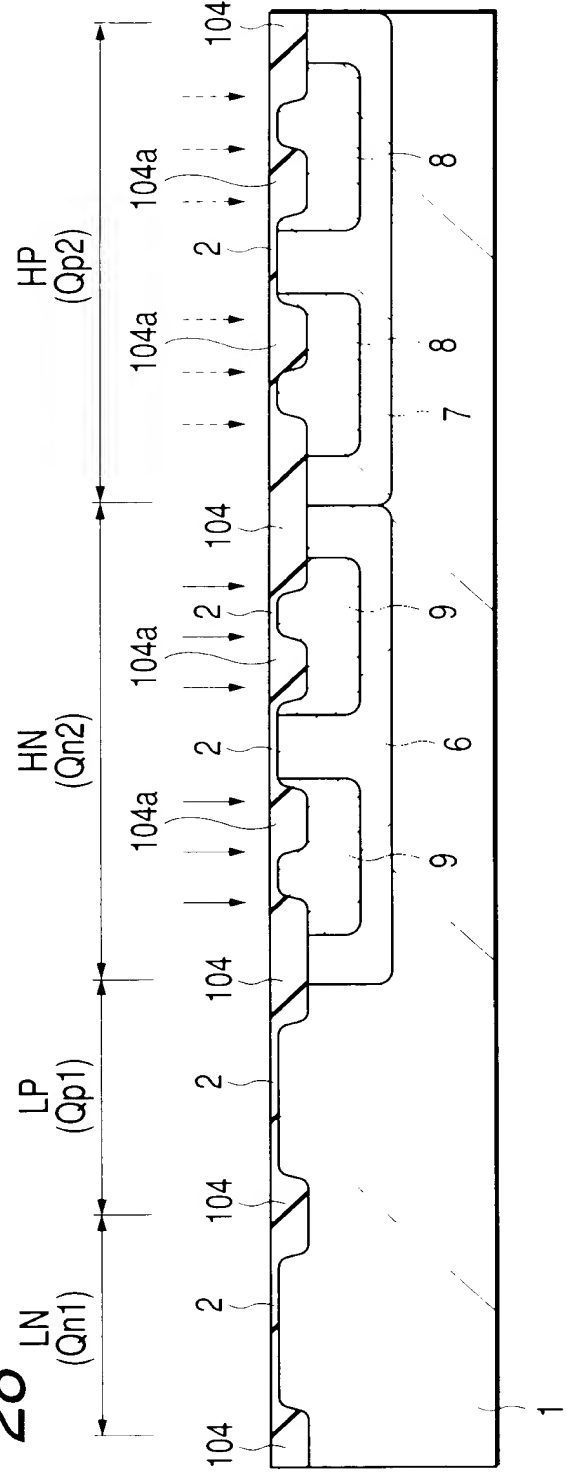


FIG. 28



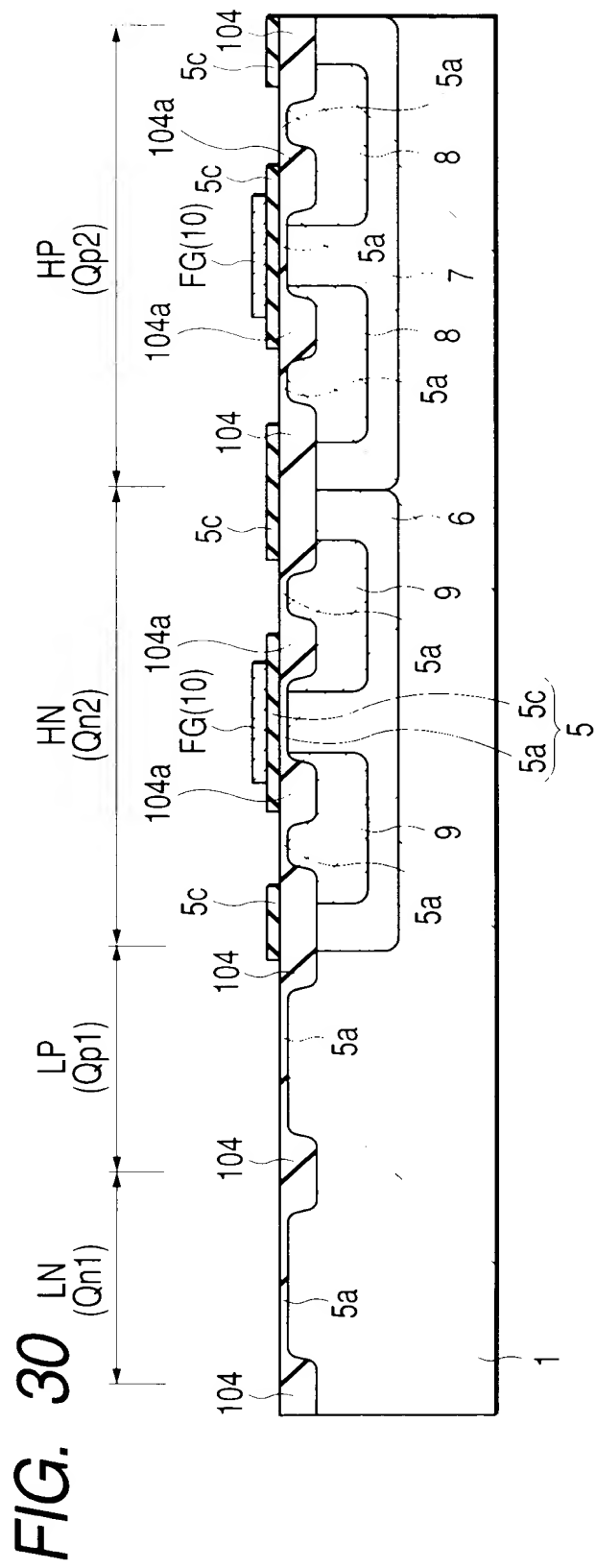
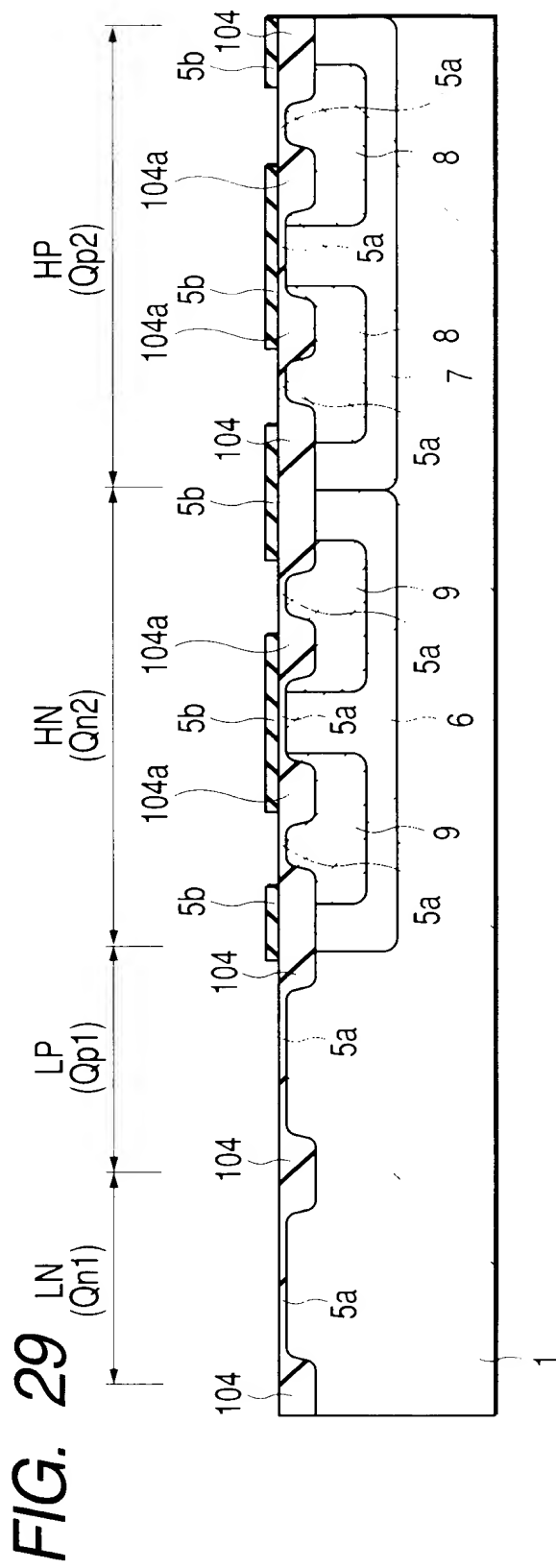


FIG. 33(a)

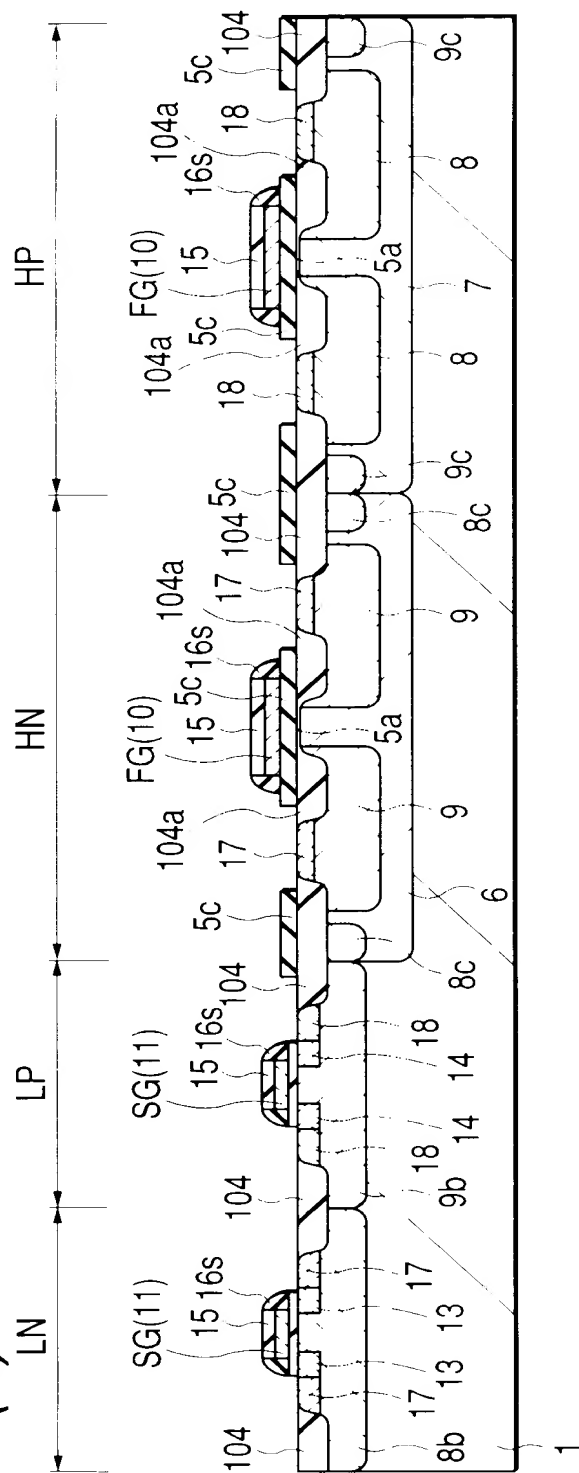


FIG. 33(b)

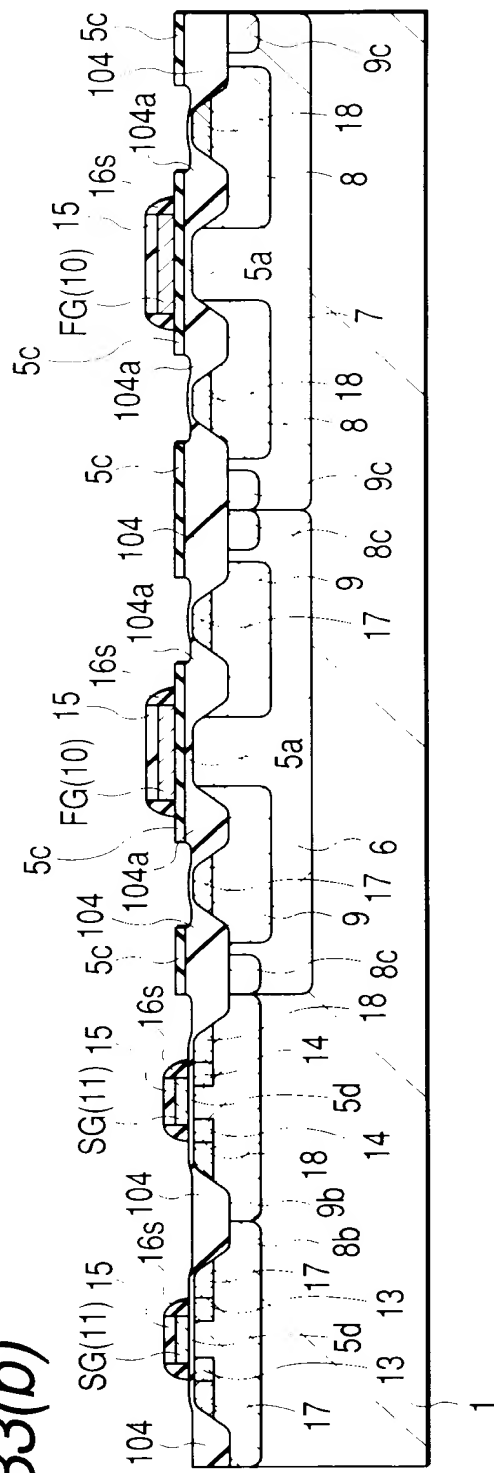


FIG. 38

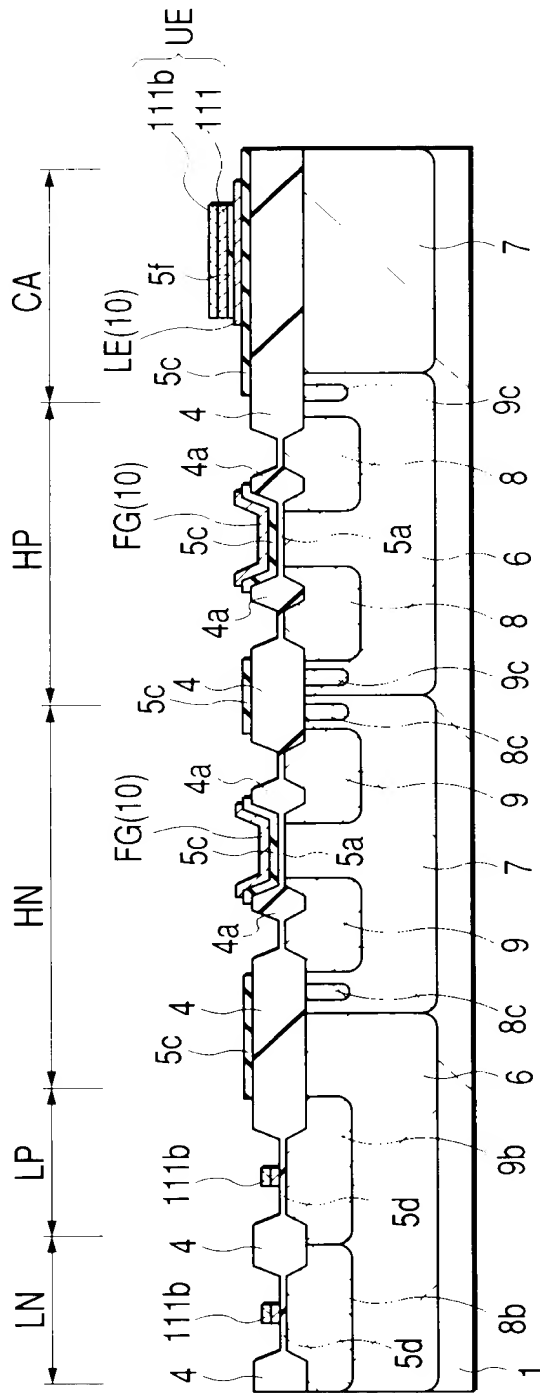


FIG. 39

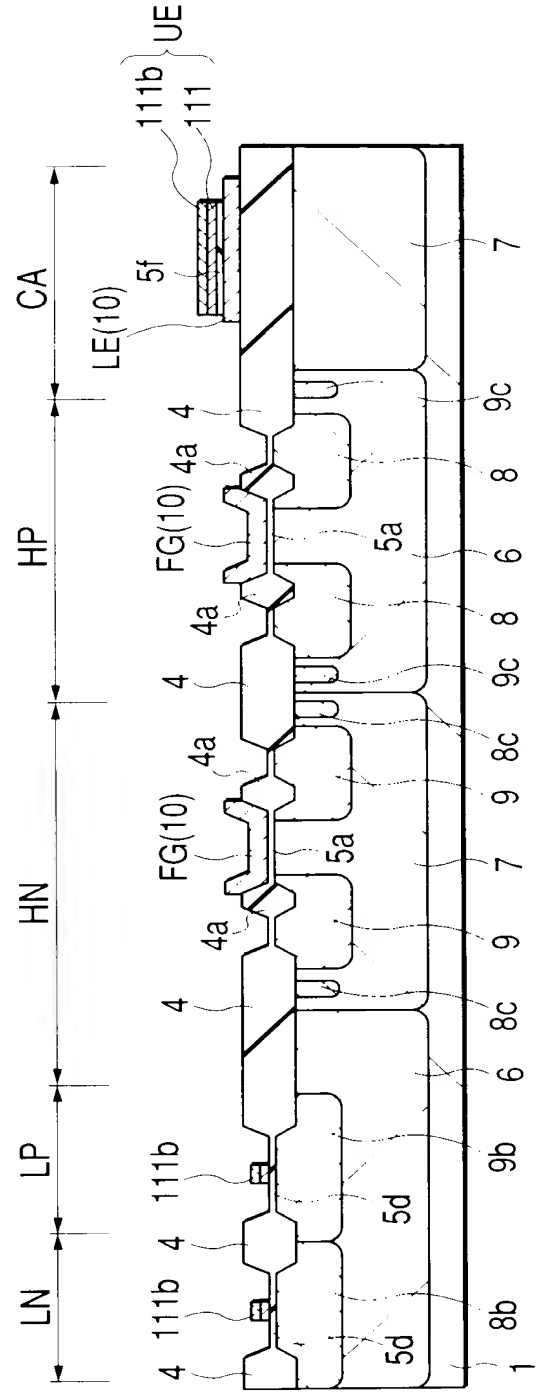


FIG. 40

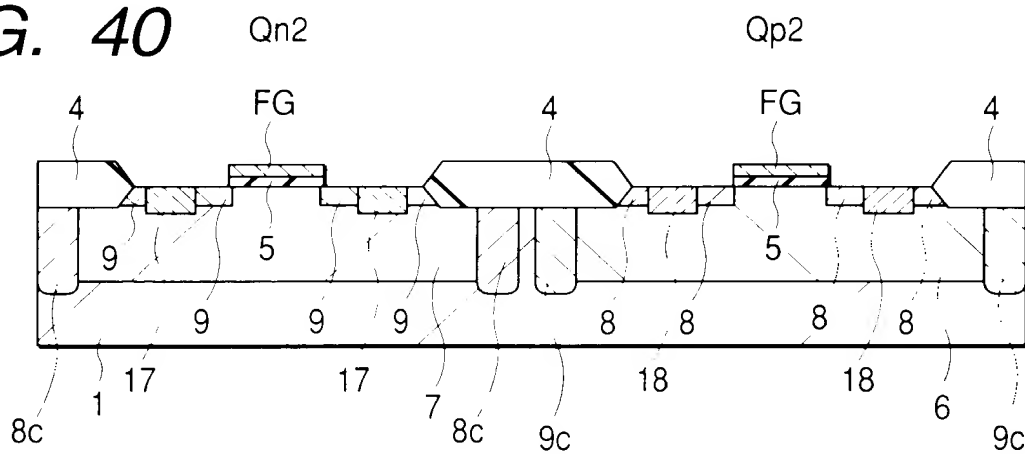


FIG. 41

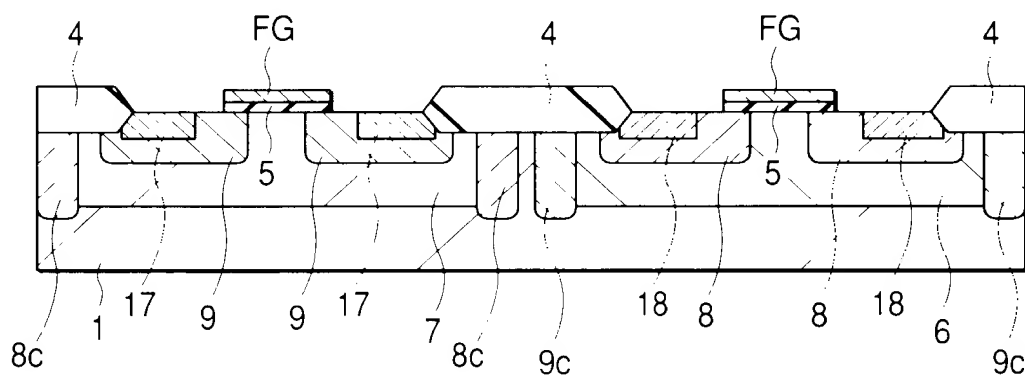


FIG. 42

